TOSHIBA

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

FEATURES

HIGH POWERT

P1dB=36.0dBm at 5.9GHz to 6.75GHz

HIGH GAIN

G1dB=8.0dB at 5.9GHz to 6.75GHz

MICROWAVE POWER GaAs FET TIM5964-4SL-251 PRELIMINARY

- BROAD BAND INTERNALLY MATCHED
- HERMETICALLY SEALED PACKAGE

RF PERFORMANCE SPECIFICATIONS $(Ta = 25^{\circ}C)$

CHARACTERISTICS	SYMBOL	CONDITION	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB	P1dB		dBm	35.5	36.5	
Compression Point						
Power Gain at 1dB	G1dB	VDS= 10V	dB	8.0		
Compression Point		f= 5.9 to 6.75GHz				
Drain Current	IDS1		А		1.1	1.3
Gain Flatness	ΔG		dB			±0.6
Power Added Efficiency	η_{add}		%		32	
3 rd Order Intermodulation	IM3		dBc	-42	-45	
Distortion		NOTE				
Drain Current	IDS2		Α		1.1	1.3
Channel Temperature Rise	ΔTch	VDS X IDS X Rth(c-c)	°C			80

NOTE : Two Tone Test, Po=25.5dBm (Single Carrier Level)

ELECTRICAL CHARACTERISTICS $(Ta = 25^{\circ}C)$

CHARACTERISTICS	SYMBOL	CONDITION	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V	mS	_	900	_
		IDS= 1.5A				
Pinch-off Voltage	VGSoff	VDS= 3V	V	-1.0	-2.5	-4.0
		IDS= 15mA				
Saturated Drain Current	IDSS	VDS= 3V	Α	_	2.6	3.5
		VGS= 0V				
Gate-Source Breakdown	VGSO	IGS= -50μΑ	V	-5		
Voltage						
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W		4.5	6.5

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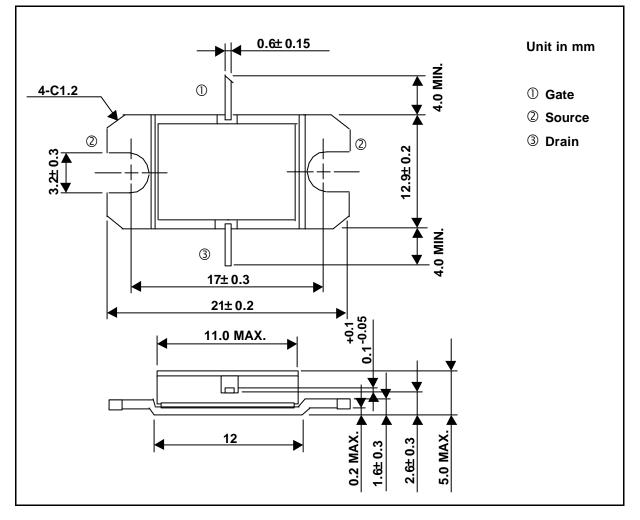
The information contained herein is subject to change without prior notice. It is therefor advisable to contact TOSHIBA before proceeding with design of equipment incorporating this product.

TIM5964-4SL-251

ABSOLUTE MAXIMUM RATINGS ($Ta = 25^{\circ}C$)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	А	3.5
Total Power Dissipation (Tc= 25 °C)	РТ	W	23.0
Channel Temperature	Tch	°C	175
Storage Temperature	Tstg	°C	-65 to +175

PACKAGE OUTLINE (2-11D1B)



HANDLING PRECAUTIONS FOR PACKAGED TYPE

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C.